



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-03B Plastic-Encapsulate Transistors

TSC114YNND03 TRANSISTOR

DESCRIPTION

NPN Digital Transistor

FEATURES

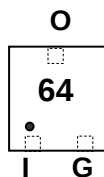
- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on/off conditions need to be set for operation, making device design easy.

APPLICATION

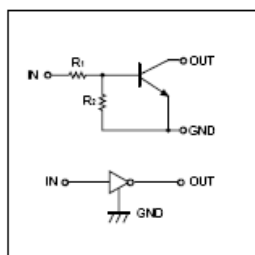
NPN Digital Transistor

For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

MARKING: 64



equivalent circuit

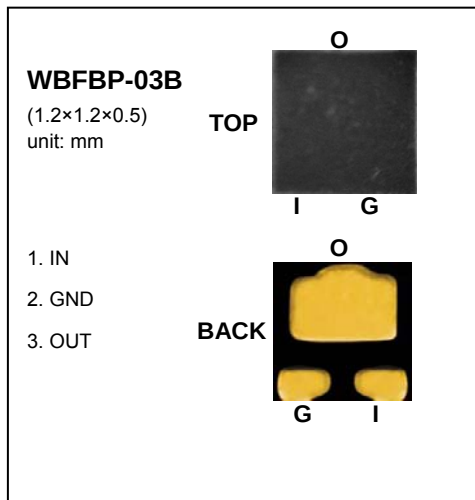


Absolute maximum ratings(Ta=25°C)

Parameter	Symbol	Limits	Unit
Supply voltage	V_{CC}	50	V
Input voltage	V_{IN}	-6to+40	V
Output current	I_O	70	mA
	$I_{C(Max.)}$	100	mA
Power dissipation	P_C	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to+ 150	°C

Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Input voltage	$V_{I(off)}$			0.3	V	$V_{CC}=5V, I_O=100\mu A$
	$V_{I(on)}$	1.4				$V_O=0.3V, I_O=1mA$
Output voltage	$V_{O(on)}$			0.3	V	$I_O/I_I=5mA/0.25mA$
Input current	I_I			0.88	mA	$V_I=5V$
Output current	$I_{O(off)}$			0.5	μA	$V_{CC}=50V, V_I=0$
DC current gain	G_I	68				$V_O=5V, I_O=5mA$
Input resistance	R_I	7	10	13	K Ω	
Resistance ratio	R_2/R_1	3.7	4.7	5.7		
Transition frequency	f_T		250		MHz	$V_O=10V, I_O=-5mA, f=100MHz$



Typical Characteristics

TSC114YNND03

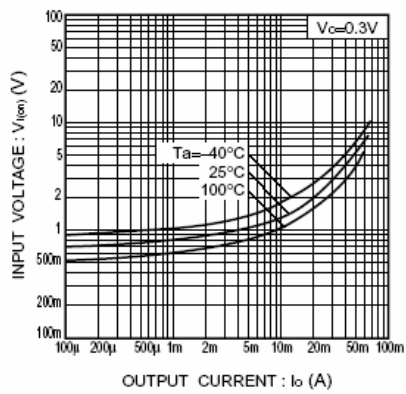


Fig.1 Input voltage vs. output current (ON characteristics)

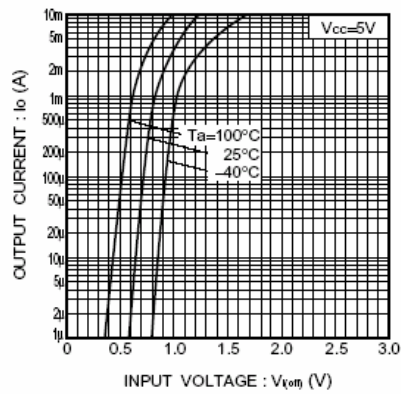


Fig.2 Output current vs. input voltage (OFF characteristics)

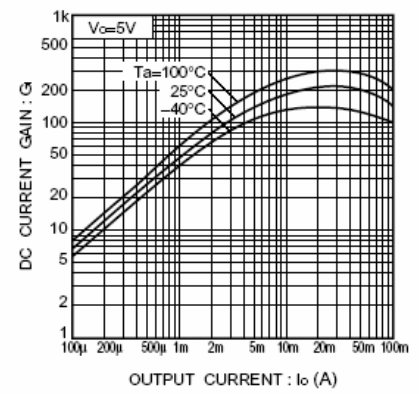


Fig.3 DC current gain vs. output current

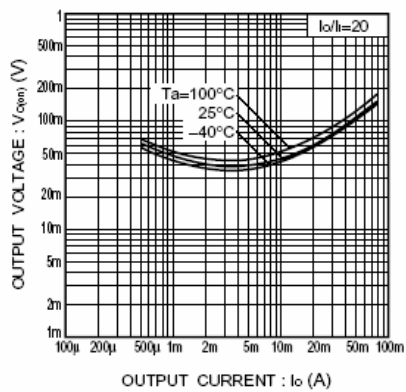


Fig.4 Output voltage vs. output current